Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)

ELECTRICAL CHARACTERISTICS (T_j=25 unles

Symbol	Test Condition	Quadrant
I_{GT}	V_D =12V R_L =33Ω	- -
V_{GT}		- -
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3kΩ	- -
I_L	I_G =1.2I_{GT}	-
I_H	I_T =500mA	
dV/dt	V_D=540V Gate Open T_j =125	
(dI/dt)c	(dV/dt)c=10V/μs T	MIN-

ORDERING INFORMATION -

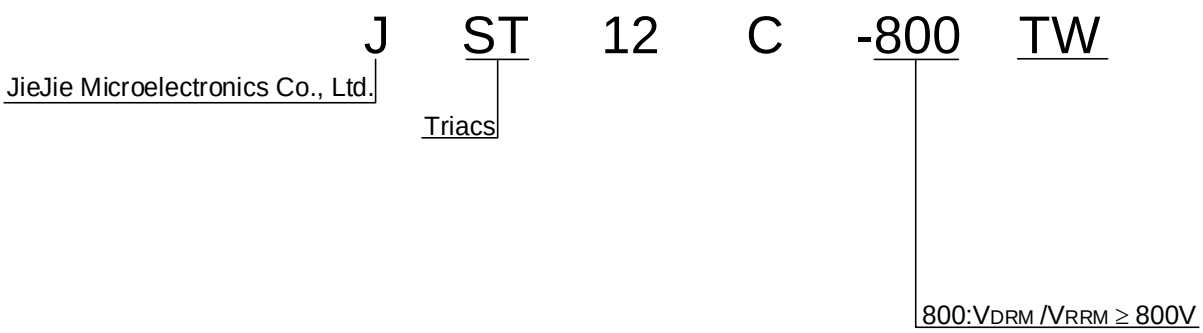


FIG.1: Maximum power dissipation versus RMS on-state current

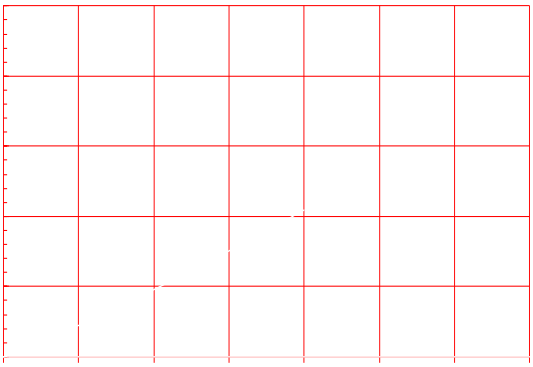


FIG.2: RMS on-state current versus case temperature

ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
JST12C-800TW	800	5	TO-220C	50	Tube -

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